

SE100P60

P-Channel Enhancement-Mode MOSFET

Revision: A

General Description

Advanced trench technology to provide excellent RDS(ON), low gate charge and low operation voltage. This device is suitable for using as a load switch or in PWM applications.

- Simple Drive Requirement
- Small Package Outline
- Surface Mount Device

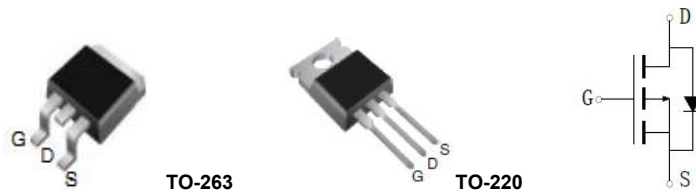
Features

For a single MOSFET

- $V_{DS} = -100V$
- $R_{DS(ON)} = 36m\Omega @ V_{GS} = -10V$

Pin configurations

See Diagram below



Absolute Maximum Ratings

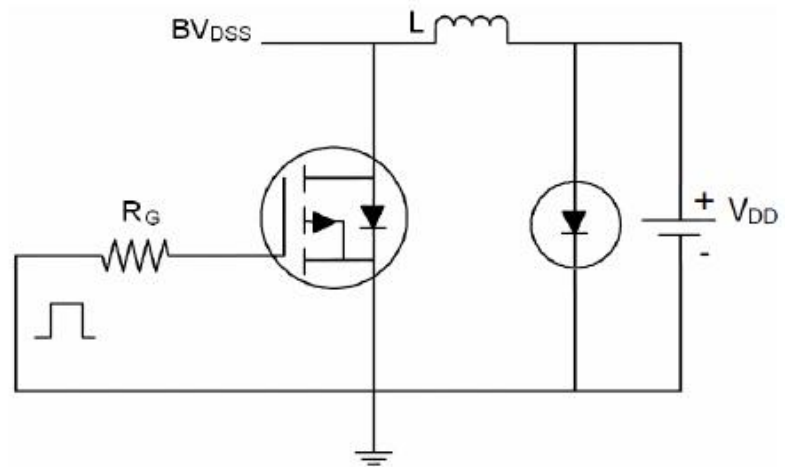
Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	-100	V
Gate-Source Voltage		V_{GS}	± 25	V
Drain Current	Continuous	I_D	-60	A
	Pulsed		-240	
Total Power Dissipation	@TA=25°C	P_D	188	W
Operating Junction Temperature Range		T_J	-55 to 150	°C

SE100P60

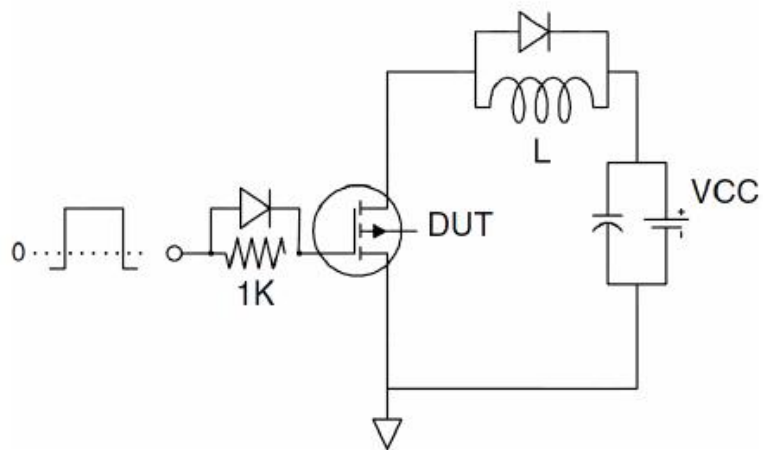
Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
B _V DSS	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0 V	-100			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = -100V, V _{GS} =0V			-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = 25V			100	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =-250μA	-2		-4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-60A	-	36	45	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-50V, I _D =-10A	5			S
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-50V, f=1MHz		4200		pF
C _{oss}	Output Capacitance			615		pF
C _{rss}	Reverse Transfer Capacitance			380		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =-10V, V _{DS} =-80V, I _D =-60A		90		nC
Q _{gs}	Gate Source Charge			15		nC
Q _{gd}	Gate Drain Charge			35		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =-10V, V _{DS} =-50V, R _{GEN} =6Ω,		27		ns
t _{d(off)}	Turn-Off Delay Time			145		ns
t _{d(r)}	Turn-On Rise Time			83		ns
t _{d(f)}	Turn-Off Fall Time			40		ns
Thermal Resistance						
Symbol	Parameter		Typ	Max		Units
R _{θJC}	Junction to Case		-	1.25		°C/W

Test Circuits and Waveform

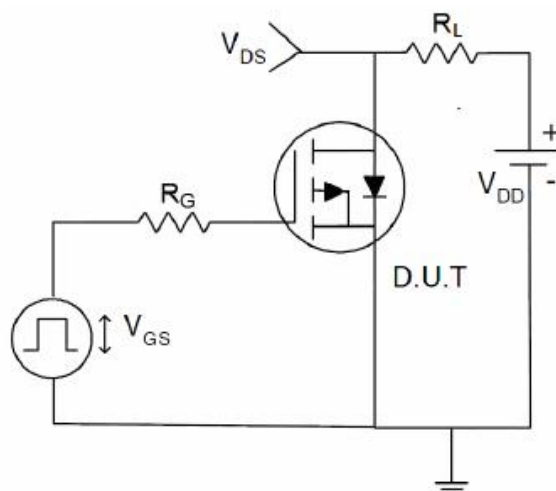
1) E_{AS} Test Circuit



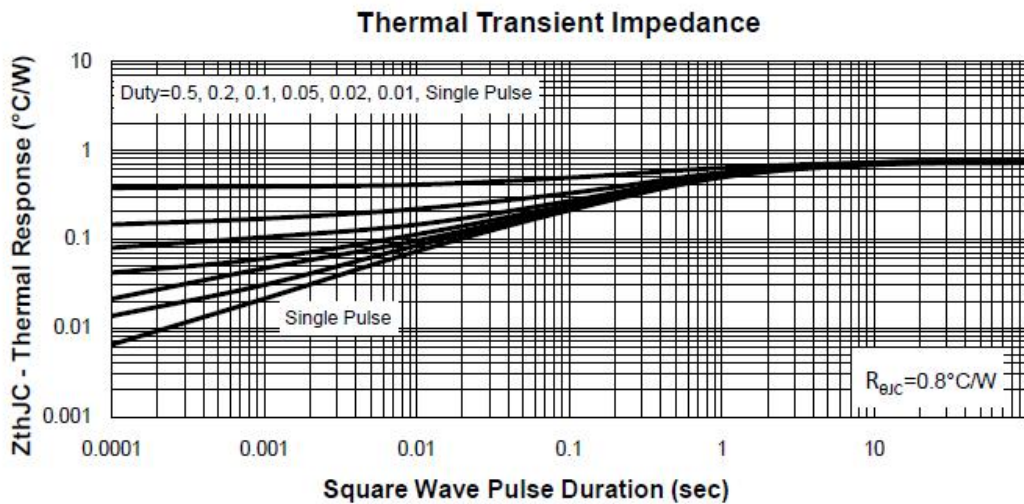
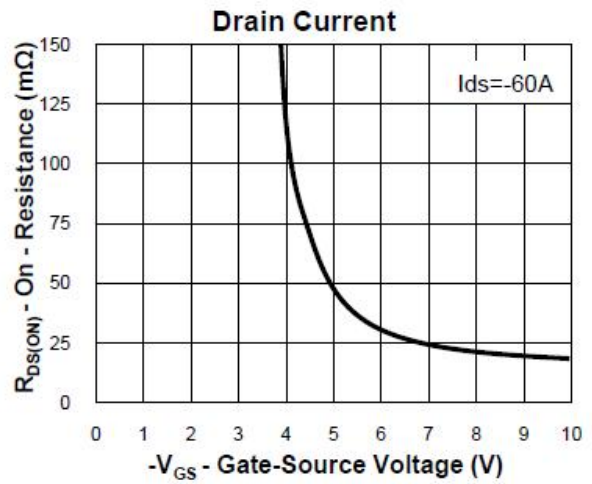
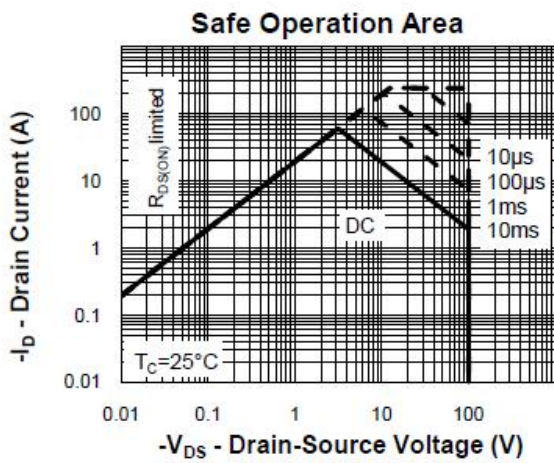
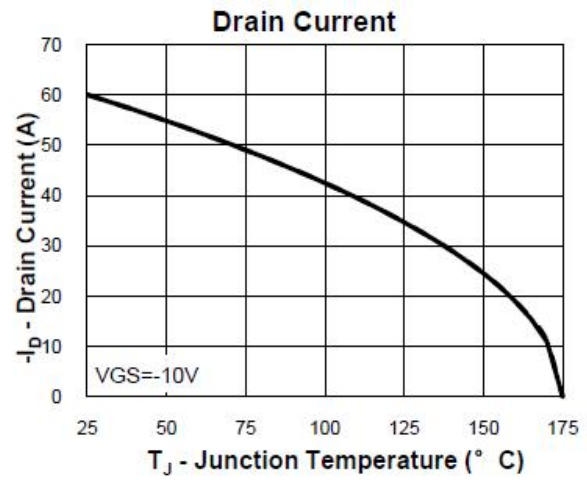
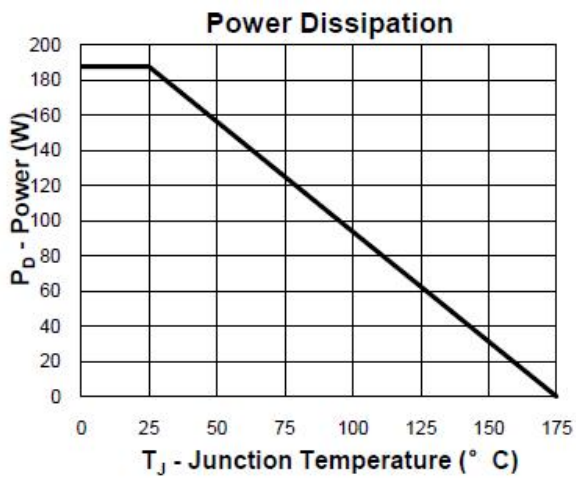
2) Gate Charge Test Circuit



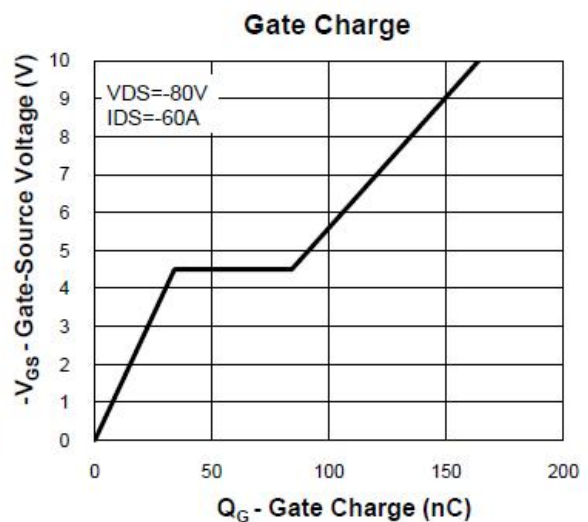
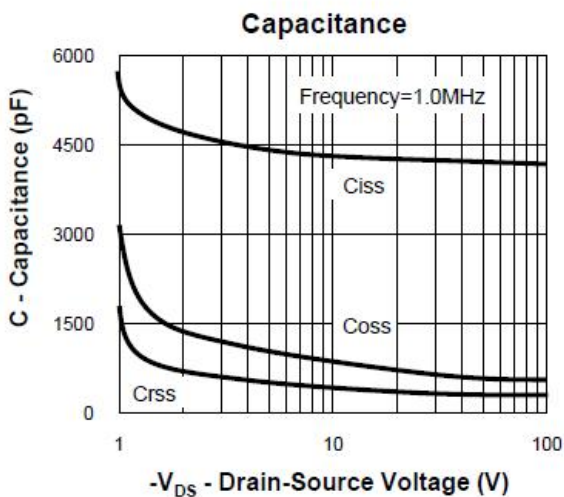
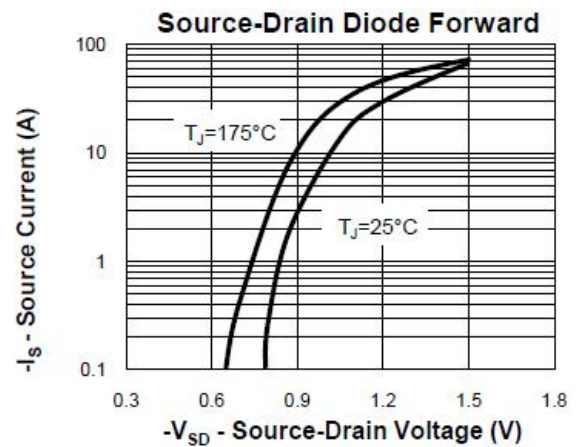
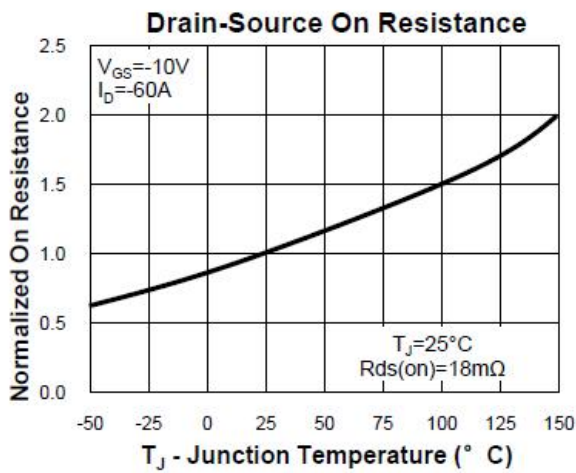
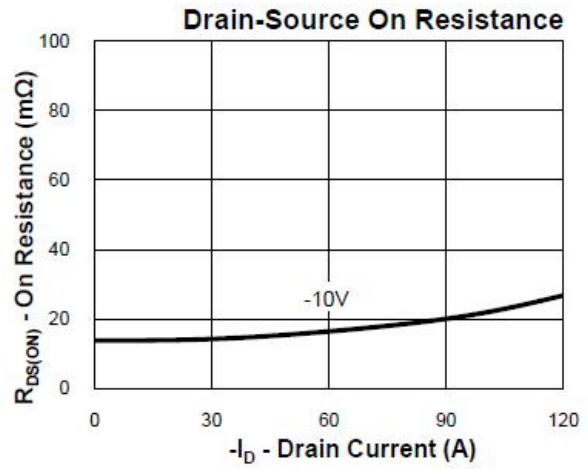
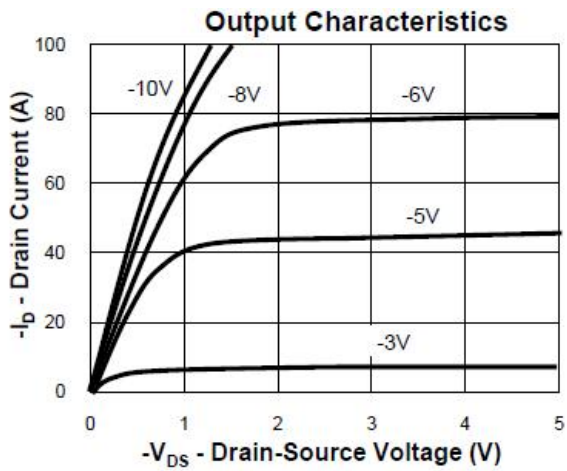
3) Switch Time Test Circuit



Typical Characteristics



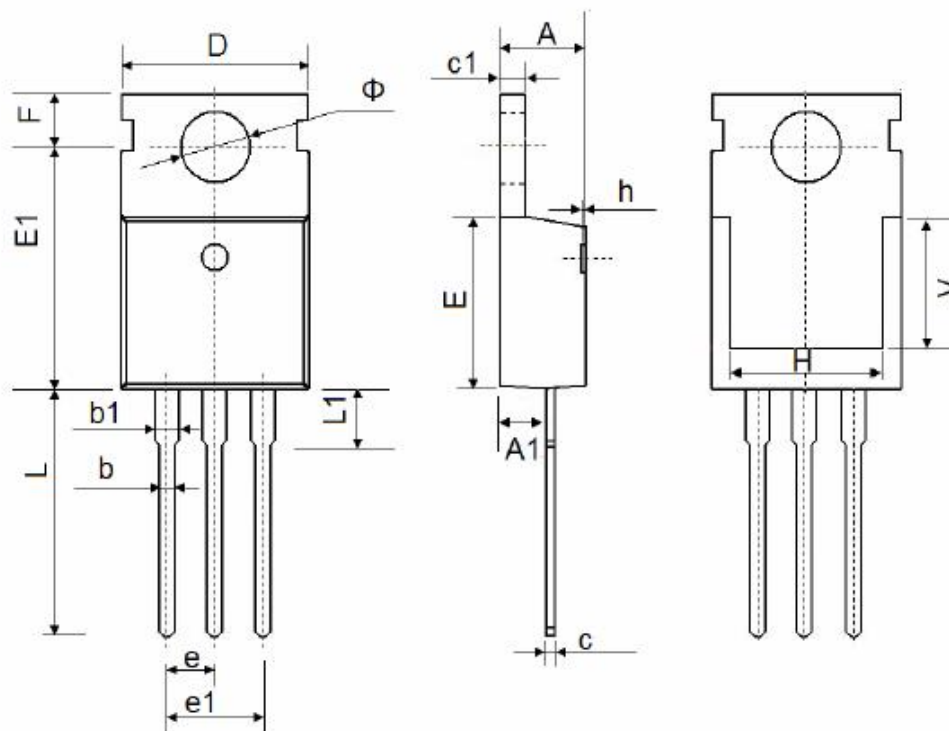
Typical Characteristics



SE100P60

Package Outline Dimension

TO-220

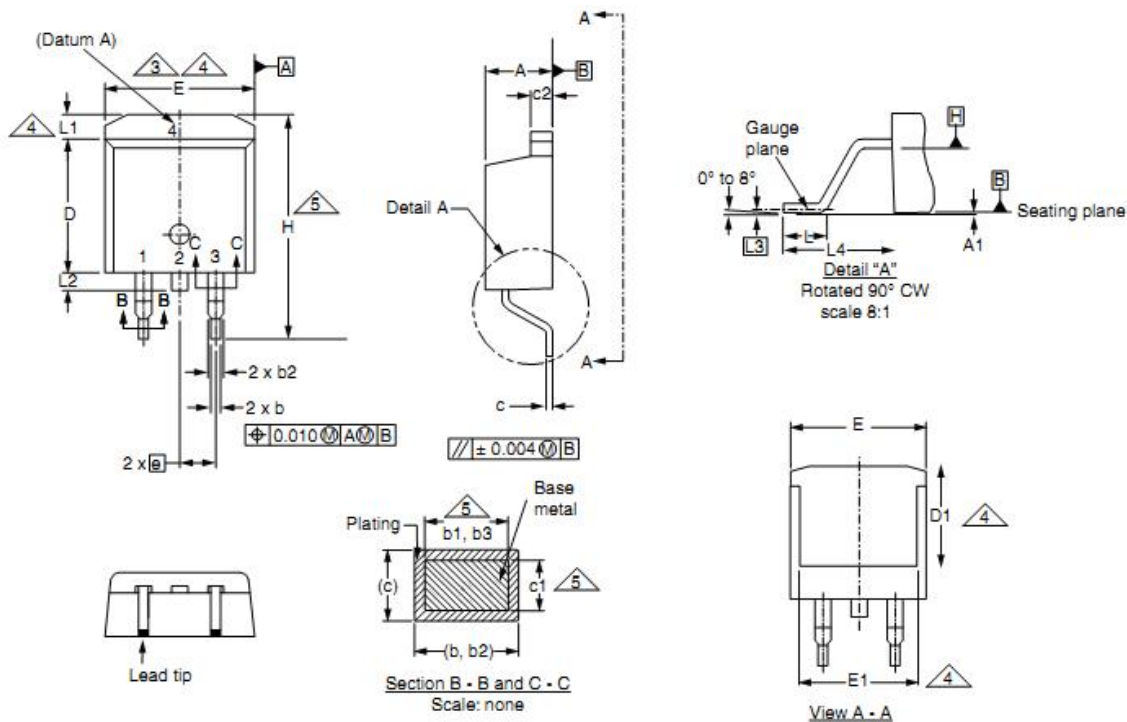


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

SE100P60

Package Outline Dimension

TO-263



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

The SINO-IC logo is a registered trademark of ShangHai Sino-IC Microelectronics Co., Ltd.

© 2005 SINO-IC – Printed in China – All rights reserved.

SHANGHAI SINO-IC MICROELECTRONICS CO., LTD

Add: Building 3, Room 3401-03, No.200 Zhangheng Road, ZhangJiang Hi-Tech Park, Pudong,
Shanghai 201203, China

Phone: +86-21-33932402 33932403 33932405 33933508 33933608

Fax: +86-21-33932401

Email: webmaster@sino-ic.net

Website: <http://www.sino-ic.net>